

C3NiT Centre Day 2019

12th of November 2019, Linköping, Sweden

8.30 – 9.00	Registration/Coffee
9.00 – 9.15	Vanya Darakchieva, Linköping University <i>Welcome address</i>
9.15 – 9.45	Jun Suda, Nagoya University <i>Development of vertical GaN power devices</i>
9.45 – 10.10	C3NiT Poster presentation rally
10.10 – 10.40	Peter Raad, Southern Methodist University <i>Thermal analysis and thermal management of electronic devices</i>
10.40 – 11.10	Coffee Break (poster session)
11.10 – 11.40	Plamen Paskov, Linköping University <i>C3NiT Project Overview and highlights: GaN doping and thermal conductivity</i>
11.40 – 12. 10	Elke Meissner, Fraunhofer IISB <i>III-N substrates and defect characterization</i>
12.10 – 12.40	Jr. Tai Chen, SweGaN AB and Linköping University <i>C3NiT Project Overview and highlights: N-polar III Nitride epitaxy and new reactor developments</i>
12.40 – 13.40	Lunch
13.40 – 14.10	Niklas Rorsman, Chalmers University of Technology <i>C3NiT Project Overview and highlights: Lateral GaN HEMTs for rf and power applications</i>
14.10 – 14.40	Sylvain Delage, III – V Lab <i>Perspective on GaN rf technology of the future</i>
14.40 – 15.00	Anna Malmros, University of Technoaogy and Gotmic AB <i>C3NiT Project Overview and highlights: GaN MMIC</i>
15.00- 15.30	Coffee Break (poster session)
15.30 – 16.00	Huili Grace Xing, Cornell University <i>GaN and Ga₂O₃ power electronics</i>
16.00 – 16.15	Jawad ul Hassan, Linköping University <i>C3NiT Project Overview and highlights: Hot-wall MOCVD of Ga₂O₃ and characterization</i>
16.15 – 16.45	Ezgi Dogmus, Yole Development <i>Overview on GaN rf and power market</i>
16.45 – 18.00	Poster session and mingle
19.00	Dinner Munkkällaren